

Comparative characteristics of diffusion-welded high-voltage stacks and connected in series Schottky diodes

Sleptšuk, Natalja; Korolkov, Oleg; Land, Raul; Toompuu, Jana; Annus, Paul; Rang, Toomas BEC 2016 : 2016 15th Biennial Baltic Electronics Conference : proceedings of the 15th Biennial Baltic Electronics Conference : Tallinn University of Technology, October 3-5, 2016, Tallinn, Estonia 2016 / p. 39-42 : ill http://www.ester.ee/record=b2150914*est

High-voltage diffusionwelded stacks on the basis of SiC Schottky diodes

Korolkov, Oleg; Sleptšuk, Natalja; Annus, Paul; Land, Raul; Rang, Toomas Silicon carbide and related materials 2015 (ICSRM 2015) : selected, peer reviewed papers from the 16th International Conference on Silicon Carbide and Related Materials, October 4-9, 2015, Giardini Naxos, Italy 2016 / p. 790-794 : ill <https://doi.org/10.4028/www.scientific.net/MSF.858.790> [Conference Proceedings at Scopus](#) [Article at Scopus](#)

SiC JBS diode symmetrical voltage doubler represented as the diffusion-welded stack

Korolkov, Oleg; Land, Raul; Toompuu, Jana; Sleptšuk, Natalja; Rang, Toomas Silicon carbide and related materials 2017 : ICSRM 2017 : selected, peer reviewed papers from the 2017 International Conference on Silicon Carbide and related materials, September 17-22, 2017, Washington, DC, USA 2018 / p. 862-865 : ill <https://doi.org/10.4028/www.scientific.net/MSF.924.862> [Conference Proceedings at Scopus](#) [Article at Scopus](#)

SIC schottky diode rectifier bridge represented as the diffusion-welded stack

Korolkov, Oleg; Kozlovski, Vitali V.; Lebedev, Alexander A.; Land, Raul; Sleptšuk, Natalja; Toompuu, Jana; Rang, Toomas Silicon Carbide and Related Materials 2016 : selected, peer reviewed papers from the 11th European Conference on Silicon Carbide and Related Materials 2016 (ECSCRM 2016), September 25-29, 2016, Halkidiki, Greece 2017 / p. 697-700 : ill <https://doi.org/10.4028/www.scientific.net/MSF.897.697> [Conference proceedings at Scopus](#) [Article at Scopus](#)